Plastic Infrared Emitting Diode

OP265FAA Series



Features:

- T-1 (3 mm) package style
- Narrow irradiance pattern
- Dome lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm diode

Description:

Each device in the **OP265FAA** series is a high intensity gallium arsenide infrared emitting diode (GaAIAs) that is molded in an IR transmissive clear epoxy package with a dome lens. Devices feature a narrow source irradiance pattern and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space-limited applications.

These devices are mechanically and spectrally matched to other OPTEK products as follows:

OP265 devices conform to the OP505 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- Space-limited applications
- Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information									
Part Number	LED Peak Wavelength	Output Power (mW/cm ²) Min / Max	I _F (mA) Typ / Max	Total Beam Angle	Lead Length				
OP265FAA		5.5 / NA		18°	0.50"				
OP265FAB	950 mm	7.5 / 12.5	20 / 50						
OP265FAC	850 nm	11.5 / 16.5	20 / 50						
OP265FAD		15.5 / NA							



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage and Operating Temperature Range	-40° C to +100° C			
Reverse Voltage	2.0 V			
Continuous Forward Current	50 mA			
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾			
Power Dissipation	100 mW ⁽²⁾			

Notes:

1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.

2. Derate linearly at 1.33 mW/° C above 25° C.

 E_{E(APT)} is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. E_{E(APT)} is not necessarily uniform within the measured area.

Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS		
Input Diod	e							
Е _{Е (АРТ)}	Apertured Radiant Incidence OP265FAA OP265FAB OP265FAC OP265FAD	5.50 7.50 11.50 15.50	- - -	- 12.5 16.5 -	mW/cm²	$I_F = 20 \text{ mA}$ Aperture = 0.081" diameter Distance = 0.590" from seating surface to aperture surface		
V _F	Forward Voltage	-	-	1.80	v	I _F = 20 mA		
I _R	Reverse Current	-	10	-	μΑ	V _R = 10 V		
λ_{P}	Wavelength at Peak Emission	-	850	-	nm	I _F = 10 mA		
$\Delta \lambda_P / \Delta T$	Spectral Shift with Temperature	-	±0.18	-	nm/°C	I _F = Constant		
θ_{HP}	Emission Angle at Half Power Points	-	18	-	Degree	I _F = 20 mA		
t _r	Output Rise Time	-	10	-	ns	I _{F(PK)} =100 mA, PW=10 μs, D.C.=10.0%		
t _f	Output Fall Time	-	10	-	ns			

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Performance

OP265F (AA, AB, AC, AD)



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